Nobuhiko Mitoma

List of Publications by Year in descending order

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| # | Article | IF | CITATIONS |
|----|---|------|-----------|
| 1 | Stable amorphous In2O3-based thin-film transistors by incorporating SiO2 to suppress oxygen vacancies. Applied Physics Letters, 2014, 104, . | 3.3 | 83 |
| 2 | Carbon Nanosheets by Morphologyâ€Retained Carbonization of Twoâ€Dimensional Assembled Anisotropic Carbon Nanorings. Angewandte Chemie - International Edition, 2018, 57, 9679-9683. | 13.8 | 80 |
| 3 | Low-temperature processable amorphous In-W-O thin-film transistors with high mobility and stability. Applied Physics Letters, 2014, 104, 152103. | 3.3 | 79 |
| 4 | Robustness of Spin Polarization in Grapheneâ€Based Spin Valves. Advanced Functional Materials, 2009, 19, 3711-3716. | 14.9 | 70 |
| 5 | Synthesis, properties, and crystal structures of π-extended double [6]helicenes: contorted multi-dimensional stacking lattice. Organic and Biomolecular Chemistry, 2017, 15, 4697-4703. | 2.8 | 61 |
| 6 | Dopant selection for control of charge carrier density and mobility in amorphous indium oxide thin-film transistors: Comparison between Si- and W-dopants. Applied Physics Letters, 2015, 106, . | 3.3 | 56 |
| 7 | Photo-oxidation of Graphene in the Presence of Water. Journal of Physical Chemistry C, 2013, 117, 1453-1456. | 3.1 | 45 |
| 8 | Coexistence of Dirac-cone states and superconductivity in iron pnictide Ba(Fe1â^'xRuxAs)2. Physical Review B, 2011, 84, . | 3.2 | 27 |
| 9 | Suppression of excess oxygen for environmentally stable amorphous In-Si-O thin-film transistors. Applied Physics Letters, 2015, 106, . | 3.3 | 25 |
| 10 | Codoping of zinc and tungsten for practical high-performance amorphous indium-based oxide thin film transistors. Journal of Applied Physics, 2015, 118, . | 2.5 | 23 |
| 11 | Reduction of the interfacial trap density of indium-oxide thin film transistors by incorporation of hafnium and annealing process. AIP Advances, 2015, 5, . | 1.3 | 16 |
| 12 | Hole-transporting materials based on thiophene-fused arenes from sulfur-mediated thienannulations. Materials Chemistry Frontiers, 2018, 2, 275-280. | 5.9 | 16 |
| 13 | Perfluorocycloparaphenylenes. Nature Communications, 2022, 13, . | 12.8 | 16 |
| 14 | Self-formed copper oxide contact interlayer for high-performance oxide thin film transistors. Applied Physics Letters, 2014, 105, . | 3.3 | 13 |
| 15 | Phase transitions from semiconductive amorphous to conductive polycrystalline in indium silicon oxide thin films. Applied Physics Letters, 2016, 109, . | 3.3 | 13 |
| 16 | Gate-controlled ultraviolet photo-etching of graphene edges. Applied Physics Letters, 2013, 103, . | 3.3 | 12 |
| 17 | Enhanced sensing response of oxidized graphene formed by UV irradiation in water. Nanotechnology, 2015, 26, 105701. | 2.6 | 10 |
| 18 | Analysis of Degradation in Graphene-Based Spin Valves. Applied Physics Express, 2009, 2, 123004. | 2.4 | 9 |

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Νοβυμικό Μιτομα

| # | Article | IF | CITATIONS |
|----|--|-----|-----------|
| 19 | Controllable film densification and interface flatness for high-performance amorphous indium oxide based thin film transistors. Applied Physics Letters, 2014, 105, . | 3.3 | 9 |
| 20 | Gate-controlled photo-oxidation of graphene for electronic structure modification. Journal of Materials Chemistry C, 2019, 7, 1904-1912. | 5.5 | 7 |
| 21 | Spin injection and detection in a graphene lateral spin valve using an yttrium-oxide tunneling barrier. Applied Physics Express, 2014, 7, 085101. | 2.4 | 6 |
| 22 | Influence of Al2O3 layer insertion on the electrical properties of Ga-In-Zn-O thin-film transistors. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2015, 33, . | 2.1 | 6 |
| 23 | Effect of carbon doping on threshold voltage and mobility of In-Si-O thin-film transistors. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2018, 36, 061206. | 1.2 | 5 |
| 24 | Correlation between active layer thickness and ambient gas stability in IGZO thin-film transistors. Journal Physics D: Applied Physics, 2017, 50, 025102. | 2.8 | 4 |